

SE3082G

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

Thigh Density Cell Design For Ultra Low On-Resistance Fully Characterized Avalanche Voltage and Current Improved Shoot-Through FOM

- Simple Drive Requirement
- Small Package Outline
- Surface Mount Device

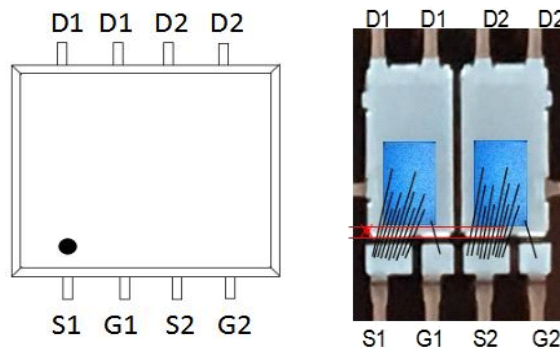
Features

For a single MOSFET

- $V_{DS} = 30V$
- $R_{DS(ON)} = 5.0m\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	80	A
	Pulsed		170	
Total Power Dissipation	@TA=25°C	P_D	3.1	W
Operating Junction Temperature Range		T_J	-55 to 150	°C

Thermal Resistance

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Junction to Case	-	1	°C/W
$R_{\theta JA}$	Junction to Ambient	-	40	°C/W

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	30			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} =32V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	1	1.6	3	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =25A	-	5.0	7.5	mΩ
		V _{GS} =4.5V, I _D =25A		7.5	9	
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =24A	20			S
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		2330		pF
C _{oss}	Output Capacitance			460		pF
C _{rss}	Reverse Transfer Capacitance			230		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =10V, I _D =30A		51		nC
Q _{gs}	Gate Source Charge			14		nC
Q _{gd}	Gate Drain Charge			11		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =10V, R _{GEN} =2.7Ω I _D =30A		20		ns
t _{d(off)}	Turn-Off Delay Time			60		ns
t _{d(r)}	Turn-On Rise Time			15		ns
t _{d(f)}	Turn-Off Fall Time			10		ns

Typical Characteristics

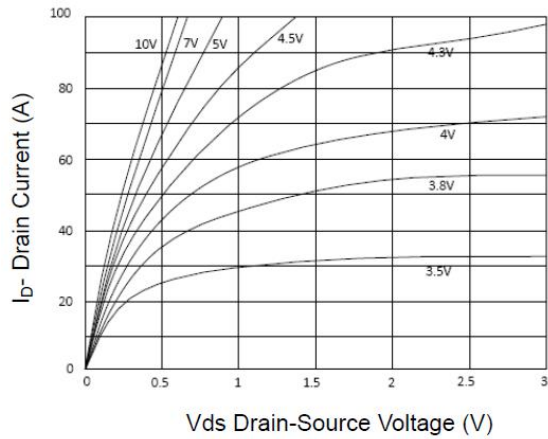


Figure 1 Output Characteristics

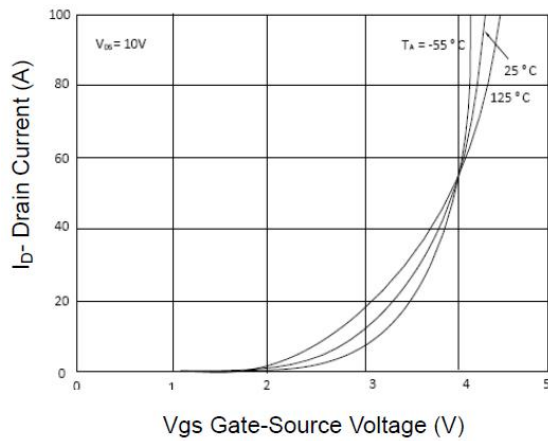


Figure 2 Transfer Characteristics

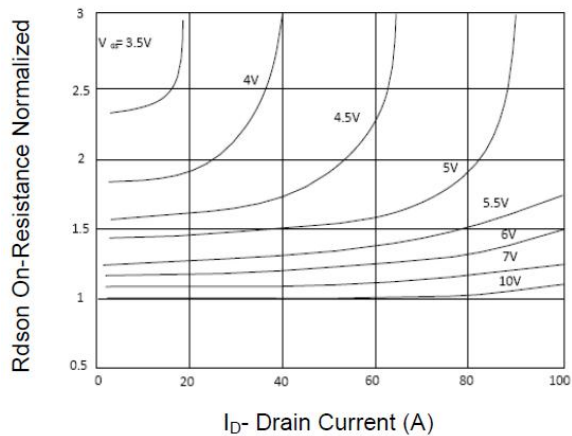
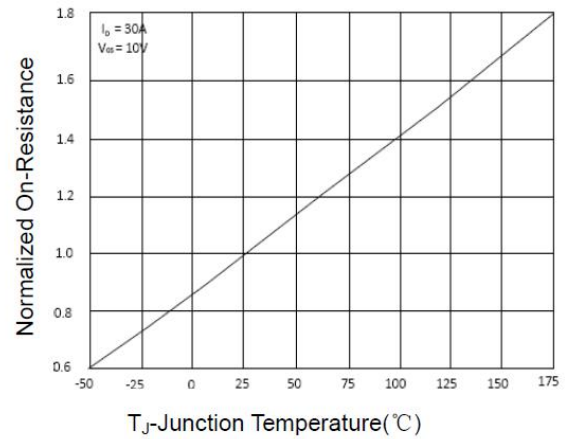
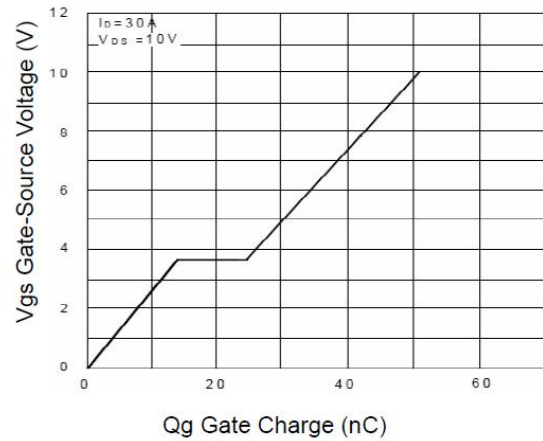
Figure 3 $R_{DS(on)}$ - Drain CurrentFigure 4 $R_{DS(on)}$ -Junction Temperature

Figure 5 Gate Charge

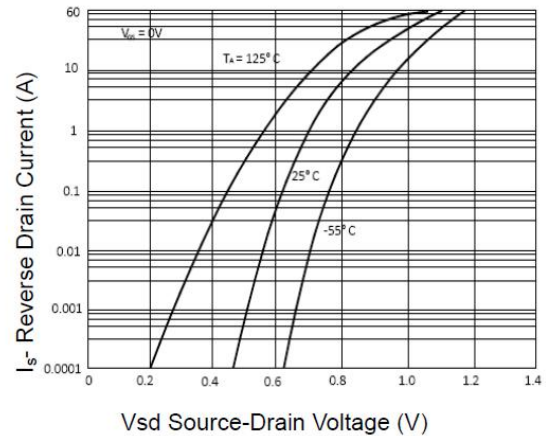


Figure 6 Source- Drain Diode Forward

Typical Characteristics

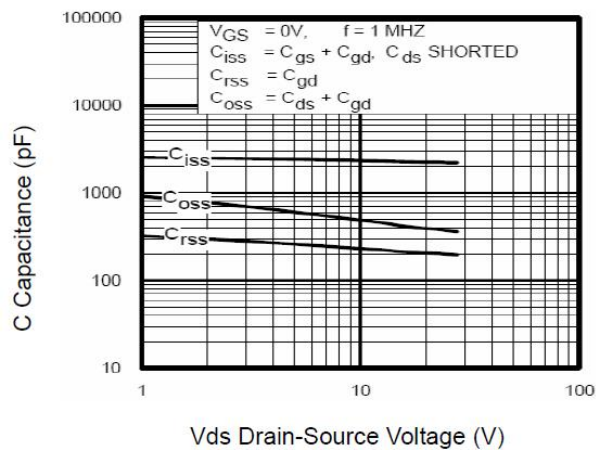
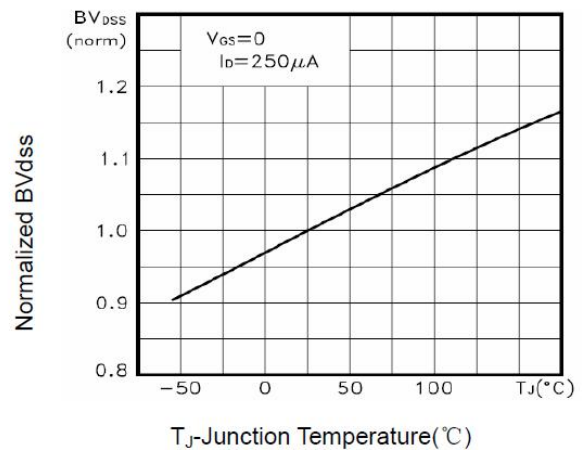
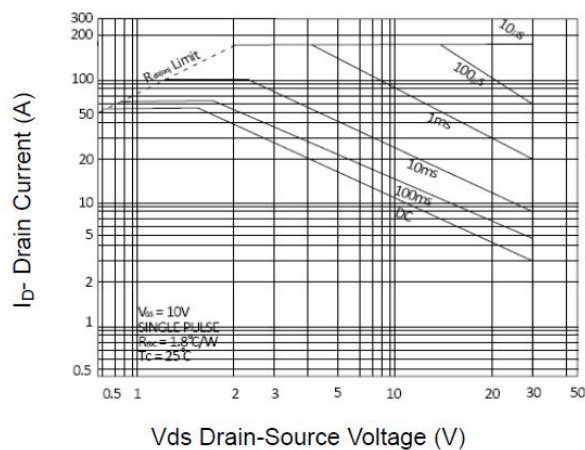
Figure 7 Capacitance vs V_{ds} Figure 9 BV_{dss} vs Junction Temperature

Figure 8 Safe Operation Area

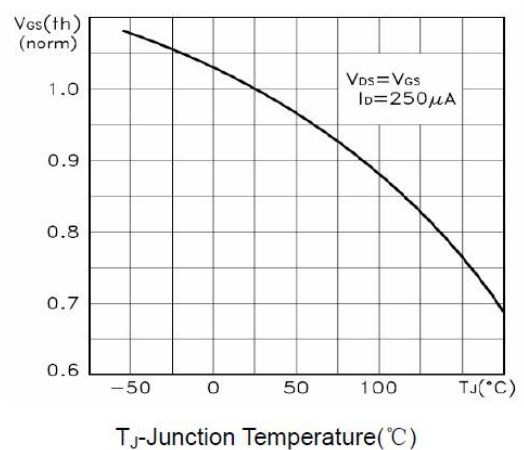
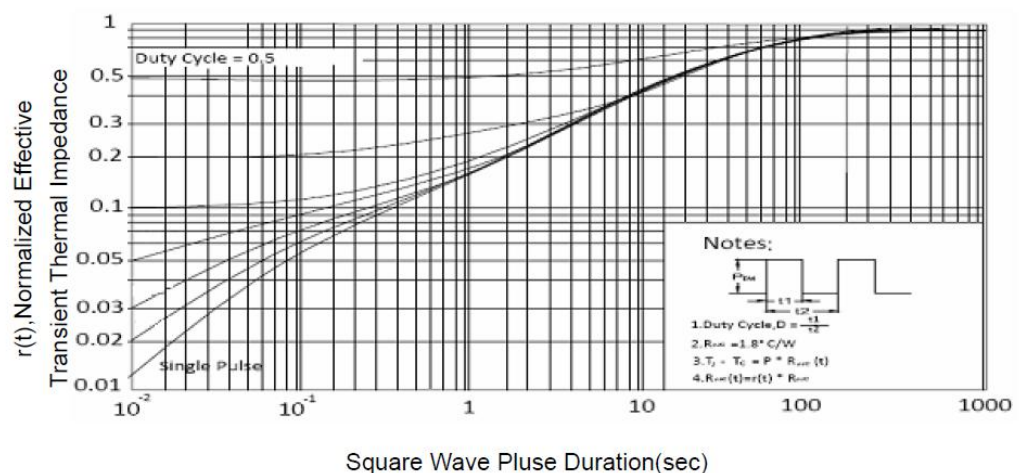
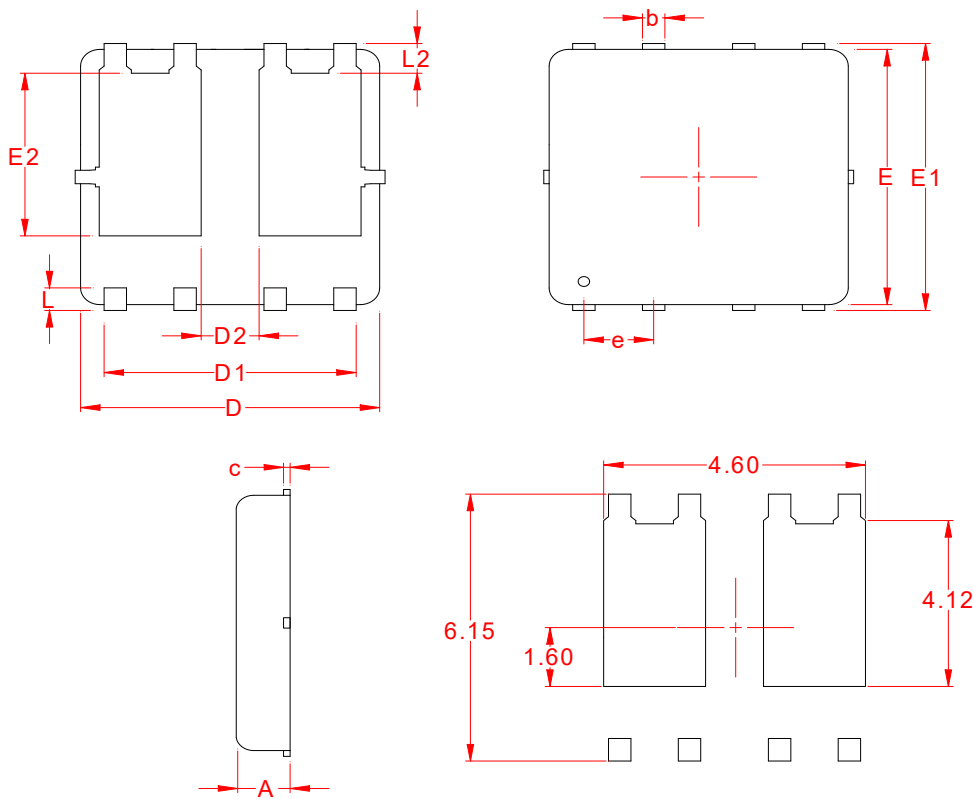
Figure 10 $V_{GS(th)}$ vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance

SE3082G

Package Outline Dimension

DFN5×6 EP2



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	—	0.05	0.000	—	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
D2	0.50	0.60	0.75	0.020	0.024	0.030
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.82 BSC			0.150 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	—	0.15	0	—	0.006
L2	0.68 REF			0.027 REF		
θ	0°	—	10°	0°	—	10°

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